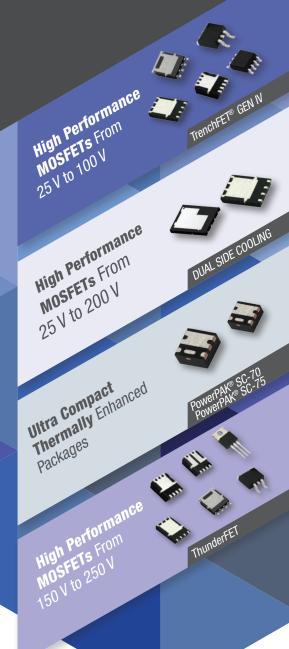


Low and Medium Voltage N-Channel MOSFETs





LOW AND MEDIUM VOLTAGE N-CHANNEL MOSFETs

Focus Products

SINGLE N-CHANNEL, 25 V to 250 V

Broad market product line; 25 V to 250 V with low $R_{DS(on)}$, excellent $R_{DS}^*Q_q$ FOM, and leadership $R_{DS}^*C_{oss}$ FOM in a wide array of package options

V _{DS} (V)	TO-247	TO-220	D ² PAK (TO-263)		PowerPAK® LITTLE FOOT®						FOOT®
			7L	3L	Dual Cool	SO-8	SO-8L	1212-8	SC-70	SO-8	TSOP-6
			*	Q	◇		4		W.	100	A
250		31 mΩ		31 mΩ		54 mΩ					
200	9.5 mΩ	15.2 mΩ		15 mΩ	31.9 mΩ	31.9 mΩ		105 mΩ	1380 mΩ		
150	5.4 mΩ	9.4 mΩ		9 mΩ	17.7 mΩ	17.7 mΩ	23.2 mΩ	58 mΩ	177 mΩ		
125						11.5 mΩ		29.8 mΩ			
100		4 mΩ	3.8 mΩ	4 mΩ	4.8 mΩ	4.8 mΩ	8 mΩ	14.4 mΩ	55 mΩ	8.8 mΩ	126 mΩ
80		3.4 mΩ		3.2 mΩ	2.9 mΩ	2.9 mΩ	6.2 mΩ	19.5 mΩ			93 mΩ
60		2.3 mΩ		2.1 mΩ	1.7 mΩ	1.7 mΩ	8 mΩ	4.5 mΩ	18.5 mΩ	4.2 mΩ	
40		1.6 mΩ		1.4 mΩ	0.88 mΩ	0.88 mΩ	1.35 mΩ	1.98 mΩ	12.5 mΩ	2.4 mΩ	
30					0.62 mΩ	0.62 mΩ		1.2 mΩ	8.4 mΩ	3.4 mΩ	
25					0.58 mΩ	0.58 mΩ		1.2 mΩ	5.6 mΩ		

Lowest maximum $R_{\mathrm{DS(on)}}$ specifications

Featured Products, Single Channel

- SiRA20DP: the lowest $R_{DS(on)}$ 25 V device; less than 0.58 m Ω
- \bullet SiSS04DN: the lowest R $_{DS(on)}$ 30 V in 3 mm x 3 mm; less than 1.2 m Ω
- \bullet SiSS12DN: the lowest R $_{\text{DS(on)}}$ 40 V in 3 mm x 3 mm; less than 1.98 m $\!\Omega$
- SiR626DP: high performance 60 V in 6 mm x 5 mm; double-cooled version is available (SiDR626DP)

DUAL N-CHANNEL, 30 V to 150 V

Low $R_{\tiny{DS(on)}}$, compact form factor, integrates two MOSFETs

Dual N-Channel MOSFETs											
Powe	rPAK® 1212-8SCD		Р	owerPAK® 1212-	-8	PowerPAK® SO-8					
С		Dual		Dual							
Part Number	V _{DS} (V)	$R_{S1-S2(on)}(\Omega)$ $V_{GS} = 10 \text{ V}$	Part Number	V _{DS} (V)	$R_{DS(on)}(\Omega)$ $V_{GS} = 10 \text{ V}$	Part Number	V _{DS} (V)	$R_{DS(on)}(\Omega)$ $V_{GS} = 10 \text{ V}$			
	30	0.005	SiSB46DN	40	0.01171	SiRB40DP	40	0.00325			
SiSF00DN			SiS990DN	100	0.085	Si7252DP	100	0.017			
						Si7946ADP	150	0.186			

Featured Products, Dual Channel

- SiSF00DN: 30 V dual common-drain; $R_{S1-S2(on)}$ is less than 5 m Ω
- SiRB40DP: 40 V dual 3.25 mΩ in PowerPAK® SO-8

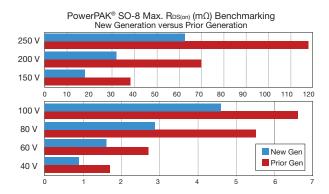


LOW AND MEDIUM VOLTAGE N-CHANNEL MOSFETs

Focus Products

Innovation for Increased Power Density and Efficiency

Breakdown Voltages: 40 V to 250 V



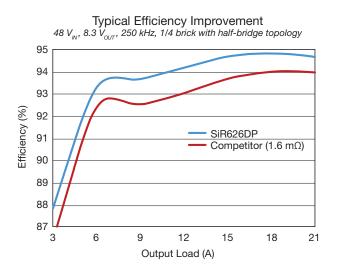
Industry's lowest R_{DS}*Q_{oss} figure-of-merit (FOM) in an advanced package array

Solution Size and Profile Reduction

Space-saving packages

SiA468DJ SiSS02DN $2.05 \text{ mm} \qquad 3.3 \text{ mm} \qquad 3.3 \text{ mm}$ Up to 37.8 A continuous I_D $10.89 \text{ mm}^2 \text{ footprint}$

Excellent Dynamic Parameters Optimize Switching Characteristics



Dual-Sided Cooling Feature



Thin Profile with 0.56 mm typical height; footprint Compatible to PowerPAK® S0-8 $R_{DS(on)}$ as low as 0.58 m Ω

Latest Technologies Provide Greater Than 50 % Lower On-Resistance Compared To Previous Generation



Advantages of Vishay Siliconix Low and Medium Voltage N-Channel MOSFETs

- 30 % lower $\rm R_{\rm DS(on)} \, x \, \, Q_{\rm g}$ FOM enables lower power losses than previous generation
- \bullet Exceptionally low ${\rm Q}_{\rm \tiny od}$ / ${\rm Q}_{\rm \tiny os}$ ratios enhance immunity to shoot-through
- Includes thermally enhanced PowerPAK® packaging for increased power densities
- Wide range of compact package sizes for optimization in a variety of applications

For the Following **Applications**

- DC/DC converters
- DC/AC inverters and motor drive controls
- Synchronous rectification
- · OR-ing, eFuse
- Battery management and protection



Providing high performance, thermally enhanced power stage solutions for today's power conversion topologies



An extensive range of solutions to achieve high efficiency and reliability



- www.vishay.com/mosfets/trenchfet-gen-iv/
- www.vishay.com/mosfets/medium-voltage/

Facte

- Vishay's n-channel MOSFETs with optimized R_{DS(on)}, Q_{gd}, and Q_{OSS} increase efficiency by balancing conduction and switching power losses
- Vishay is your true one-stop shop for building blocks in power conversion by providing high performance MOSFETs from 30 V to 650 V and power passive components



